

SILICON
TRANSISTORS

TO-92



ECB

2SB621,A (PNP) & 2SD592,A (NPN) are complementary silicon planar epitaxial transistors designed for AF output amplifiers.

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage
Collector-Emitter Voltage
Emittter-Base Voltage
Collector Current
Total Power Dissipation
Operating Junction & Storage Temperature

VCBO
VCEO
VEBO
IC
Ptot
Tj,Tstg

2SD592	2SD592A
30V	60V
25V	50V
	5V
	1A
750mW	
-55 to +150°C	

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITION
Collector Cutoff Current	ICBO		100	nA	VCB=20V IE=0
Collector-Base Breakdown Voltage	BVCBO	30		V	IC=10μA IE=0
	2SB621 /2SD592	60			
	2SB621A/2SD592A				
Collector-Emitter Breakdown Voltage	LVCEO	25		V	IC=2mA IB=0
	2SB621 /2SD592	50			
	2SB621A/2SD592A				
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=10μA IC=0
D.C. Current Gain	HFE	85	340		IC=500mA VCE=10V*
		50			IC=1A VCE=10V*
Collector-Emitter Saturation Voltage	VCE(sat)		0.4	V	IC=500mA IB=50mA*
Base-Emitter Saturation Voltage	VBE(sat)		1.2	V	IC=500mA IB=50mA*
Current Gain Bandwidth Product	fT	200	TYP	MHz	IC=50mA VCE=10V
Output Capacitance	Cob		30	pF	VCB=10V f=1MHz
	2SB621,A		20	pF	
	2SD592,A				

Pulse Test : Pulse Width < 300μs, Duty Cycle < 1%.

HFE Grouping

Q : 85-170

R : 120-240

S : 170-340



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